

Please amend the first full paragraph on page 10 as follows:

In a key aspect of the invention, the passivation openings can be as small as 0.1  $\mu\text{m}$ .  ~~$\mu\text{m}$~~ .  
In another critical aspect of the invention, various methods are used to form the Post  
Passivation Technology segment 80, in which metal lines which are formed substantially  
thicker and wider than those in the IC Interconnection layer. More detail is provided below.

Please amend the <sup>first</sup> ~~third~~ full paragraph on page <sup>11</sup> ~~10~~ as follows:

RP  
2/5/08

In one important aspect of the current invention, referring now to FIGS. 12a-12h, and  
specifically FIG. 12a, openings 7 in the polymer layer 5 may be larger than openings 7' in the  
passivation layer 4. Openings 7' may be formed to as small as 0.1  $\mu\text{m}$ .  ~~$\mu\text{m}$~~ , and may range in  
size from between about 0.1 and 50  $\mu\text{m}$ .  ~~$\mu\text{m}$~~ . These small passivation vias 7' are  
advantageous for the following reasons:

Please amend the first full paragraph on page 14 as follows:

An adhesion layer 200 and an electroplating seed layer 202 are now formed. also as  
previously described with reference to FIG. 12a, and as shown in FIG. 13. Copper or gold  
210 is electroplated up from seed layer 202 to fill openings 7' and 7, as well as above  
polymer layer 5, as depicted in FIG. 15. Chemical mechanical planarization (CMP) is used to  
remove the plated metal 210 above polymer 5, stopping on seed layer 202. This forms via